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Date: 04 September 2024

Origin: International

Latest date for receipt of comments: 23 October 2024

Project No. 2024/02489

Responsible committee: EPL/47 Semiconductors

Interested committees:

Title: BS EN IEC 63550-2 Semiconductor devices - Neuromorphic devices

Part 2: Evaluation method of linearity in memristor devices

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Introduction

This draft standard is based on national and international discussions. Your comments on this draft are invited and will assist in the preparation of the consequent standard.

For international standards, comments will be reviewed by the relevant UK national committee before sending the consensus UK vote and comments to the international committee, which will then decide appropriate action. If the international standard is approved, it is usual for the text to be published as a British Standard.

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Template for comments and secretariat observations

Date: xx/xx/20xx	Document: ISO/DIS xxxx
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1	2	(3)	4	5	(6)	7
MB	Clause No./ Subclause No./Annex (e.g. 3.1)	Paragraph/Figure/ Table/Note	Type of comment	Commend (justification for change) by the MB	Proposed change by the MB	Secretariat observations on each comment submitted
	3.1	Definition 1	ed	Definition is ambiguous and needs clarifying.	Amend to read '...so that the mains connector to which no connection...'	
	6.4	Paragraph 2	te	The use of the UV photometer as an alternative cannot be supported as serious problems have been encountered in its use in the UK.	Delete reference to UV photometer.	



47/2871/CD

COMMITTEE DRAFT (CD)

PROJECT NUMBER: IEC 63550-2 ED1	
DATE OF CIRCULATION: 2024-08-30	CLOSING DATE FOR COMMENTS: 2024-11-22
SUPERSEDES DOCUMENTS: 47/2811/NP, 47/2836/RVN	

IEC TC 47 : SEMICONDUCTOR DEVICES	
SECRETARIAT: Korea, Republic of	SECRETARY: Mr Cheolung Cha
OF INTEREST TO THE FOLLOWING COMMITTEES:	HORIZONTAL FUNCTION(S):
ASPECTS CONCERNED:	

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TITLE: Semiconductor devices - Neuromorphic devices - Part 2: Evaluation method of linearity in memristor devices

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INTERNATIONAL ELECTROTECHNICAL COMMISSION

**SEMICONDUCTOR DEVICES –
NEUROMORPHIC DEVICES –****Part 2:- Evaluation method of linearity in memristor devices**

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International Standard IEC 63550-2-X has been prepared by technical committee 47: Semiconductor devices.

The text of International Standard is based on the following documents:

NP	Report on voting
47/XX/NP	47/XX/NP

Full information on the voting for the approval of this standard can be found in the report on voting indicated in the above table.

The language used for the development of this International Standard is English.

This document was drafted in accordance with ISO/IEC Directives, Part 2, and developed in accordance with ISO/IEC Directives, Part 1 and ISO/IEC Directives, IEC Supplement, and the ISO/IEC Directives, JTC 1 Supplement available at www.iec.ch/members_experts/refdocs. The main document types developed by IEC are described in greater detail at www.iec.ch/publications.

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